

CLAIMS

What is claimed is:

1. A semiconductor device, comprising:

at least one contact pad positioned on a surface of the semiconductor device adjacent an edge thereof; and

a layer comprising dielectric material on at least a portion of said surface, said layer having a notch formed therein which exposes at least a portion of said at least one contact pad.

2. The semiconductor device of claim 1, wherein an edge portion of said layer adjacent said edge of the semiconductor device tapers from a surface of said layer toward said edge of the semiconductor device.

3. The semiconductor device of claim 2, wherein said edge portion of said layer comprises a bevel.

4. The semiconductor device of claim 1, wherein said at least one notch is tapered from a surface of said layer toward said surface of the semiconductor device.

5. The semiconductor device of claim 1, wherein said layer covers substantially all of said surface.

6. The semiconductor device of claim 1, wherein said at least one notch substantially surrounds said at least one contact pad.

7. The semiconductor device of claim 1, including a plurality of contact pads.

8. The semiconductor device of claim 7, wherein at least some of said contact pads are located adjacent said edge.

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9. The semiconductor device of claim 8, wherein said layer includes regions extending laterally between adjacent contact pads of said at least some contact pads.
10. The semiconductor device of claim 1, wherein said dielectric material comprises a polymer.
11. The semiconductor device of claim 1, wherein said dielectric material comprises a photoimageable material.
12. A protective layer for a semiconductor device, comprising:
a substantially planar member comprising dielectric material; and
at least one notch formed adjacent an edge of said substantially planar member, said at least one notch being configured to expose at least a portion of a corresponding contact pad of the semiconductor device upon positioning the protective layer over a surface of the semiconductor device.
13. The protective layer of claim 12, comprising a bevel along said edge.
14. The protective layer of claim 12, wherein at least one edge of said at least one notch is beveled.
15. The protective layer of claim 12, wherein said dielectric material comprises a polymer.
16. The protective layer of claim 12, wherein said dielectric material comprises a photoimageable material.
17. The protective layer of claim 12, including a plurality of notches located along said edge.

18. The protective layer of claim 12, wherein said substantially planar member is configured to substantially cover a surface of the semiconductor device upon assembly therewith.

19. The protective layer of claim 12, wherein said substantially planar structure is configured to cover only a portion of a surface of the semiconductor device adjacent an edge thereof proximate to which at least one contact pad is located upon assembly of the protective layer with the semiconductor device.

20. The protective layer of claim 12, wherein said at least one notch is formed in said edge.

21. The protective layer of claim 12, wherein said at least one notch is configured to substantially surround the corresponding contact upon assembly of the protective layer with the semiconductor device.